

Customer No.: 31561
Application No.: 10/604,627
Docket No.: 11112-US-PA

ABSTRACT AMENDMENT

Please amend the Abstract as indicated hereafter:

The present invention provides a resistance random access memory structure, ~~comprising~~including a plurality of word lines in a substrate, a plurality of reset lines
5 coupled to the word lines, a dielectric layer on the substrate, a plurality of memory units
in the dielectric layer. Each of the memory units includes a bottom electrode, a top
electrode and a resistive thin film between the top electrode and the bottom electrode.
The top electrodes of the memory units in a same column are coupled to one of the reset
lines and a plurality of the bit lines on the memory units. The bottom electrodes of the
10 memory units in a same row are coupled to one of the bit lines. Because the present
invention provides reset lines for Type 1R1D RRAM, it can overcome the non-erasable
of the conventional Type 1R1D RRAM.